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7. The method of claim 5 wherein the silicon on insulator wafer includes an insulating layer disposed between the first device layer and the handle substrate.

8. The method of claim 1 wherein the moveable element includes a light deflecting portion.

9. The method of claim 8 wherein the light deflecting portion includes a mirror.

10. A method for making a microelectromechanical combdrive device, comprising:

forming a moveable element from a first device layer;
attaching a second device layer to the first device layer
forming a first set of comb teeth from the second device
layer, wherein one or more comb teeth in the first set
extend from a major surface of the moveable element;
attaching a third device layer to the second device layer;
and

forming a second set of comb teeth from the third device
layer,

wherein the second set of comb teeth are aligned to the
first set of comb teeth by:

before attaching the third device layer to the second
device layer, forming an alignment target in the second
device layer, and

after attaching the third device layer to the second device
layer and before forming the second set of comb teeth,
forming an alignment hole in the third device layer,
wherein the alignment hole is roughly aligned to the
alignment target.

11. The method of claim 10 wherein one or more comb
teeth in the second set are configured to interdigitate with
one or more comb teeth in the first set.

12. The method of claim 10 wherein the first device layer
is part of a wafer that includes a handle substrate.

13. The method of claim 12, further comprising removing
the handle substrate after attaching the third device layer to
the second device layer.

14. The method of claim 12 wherein the handle substrate
and first device layer are part of a silicon-on-insulator wafer.

15. The method of claim 10 wherein the moveable element
includes a light deflecting portion.

16. The method of claim 15 wherein the light deflecting
portion includes a mirror.

17. A method for making a microelectromechanical
combdrive device, comprising:

forming a moveable element and a flexure from a first
device layer of a wafer having a first insulating layer
disposed between the first device layer and a handle
substrate;

forming an alignment target in the first device layer;

after forming the alignment target in the first device layer,
attaching a second device layer to the first device layer
such that the first device layer is disposed between the
insulating layer and the second device layer;

forming a second insulating layer on a surface of the
second device layer such that the second device layer is
disposed between the oxide layer and the first device
layer;

forming one or more comb teeth from the second device
layer, wherein the one or more comb teeth extend from
a major surface of the moveable element;

before attaching a third device layer to the second insu-
lating layer, forming an alignment hole through the
second insulating layer and the second device layer,
wherein the alignment hole roughly aligns with the
alignment target;

attaching the third device layer to the second insulating
layer such that the second insulating layer is disposed
between the second and third device layers;

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forming one or more comb teeth from the third device
layer, wherein the one or more comb teeth formed from
the third device layer are configured to interdigitate
with one or more of the comb teeth formed from the
second device layer; and

releasing the movable element.

18. The method of claim 17, further comprising, before
forming the comb teeth in the third device layer, removing
the handle substrate and attaching a new handle substrate to
the first insulating layer.

19. The method of claim 18 wherein the new handle
substrate is attached to the first insulating layer with a
photoresist.

20. The method of claim 18 wherein releasing the move-
able element includes releasing the new handle substrate
with a photoresist stripper.

21. The method of claim 17 wherein releasing the move-
able element includes removal of selected portions of the
first and second insulating layers.

22. A method for making a microelectromechanical
combdrive device, comprising:

forming a moveable element and a flexure from a first
device layer of a wafer having a first insulating layer
disposed between the first device layer and a handle
substrate;

attaching a second device layer to the first device layer
such that the first device layer is disposed between the
insulating layer and the second device layer;

forming a second insulating layer on a surface of the
second device layer such that the second device layer is
disposed between the oxide layer and the first device
layer;

forming one or more comb teeth from the second device
layer, wherein the one or more comb teeth extend from
a major surface of the moveable element;

before attaching a third device layer to the second insu-
lating layer, forming an alignment target in the second
device layer;

attaching the third device layer to the second insulating
layer such that the second insulating layer is disposed
between the second and third device layers;

before forming one or more comb teeth from the third
device layer, forming an alignment hole through the
third insulating layer, wherein the alignment hole
roughly aligns with the alignment target;

forming the one or more comb teeth from the third device
layer, wherein the one or more comb teeth formed from
the third device layer are configured to interdigitate
with one or more of the comb teeth formed from the
second device layer; and

releasing the movable element.

23. The method of claim 22, further comprising, before
forming the comb teeth in the third device layer, removing
the handle substrate and attaching a new handle substrate to
the first insulating layer.

24. The method of claim 23 wherein the new handle
substrate is attached to the first insulating layer with a
photoresist.

25. The method of claim 23 wherein releasing the move-
able element includes releasing the new handle substrate
with a photoresist stripper.

26. The method of claim 22 wherein releasing the move-
able element includes removal of selected portions of the
first and second insulating layers.

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